

Supplementary Information
for

Water-Penetration-Assisted Mechanical Transfer of Large-Scale Molybdenum Disulfide onto Arbitrary Substrates

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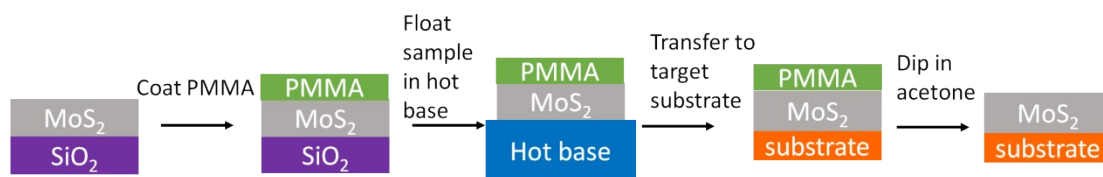


Fig. S1. Process of common solution etching method.

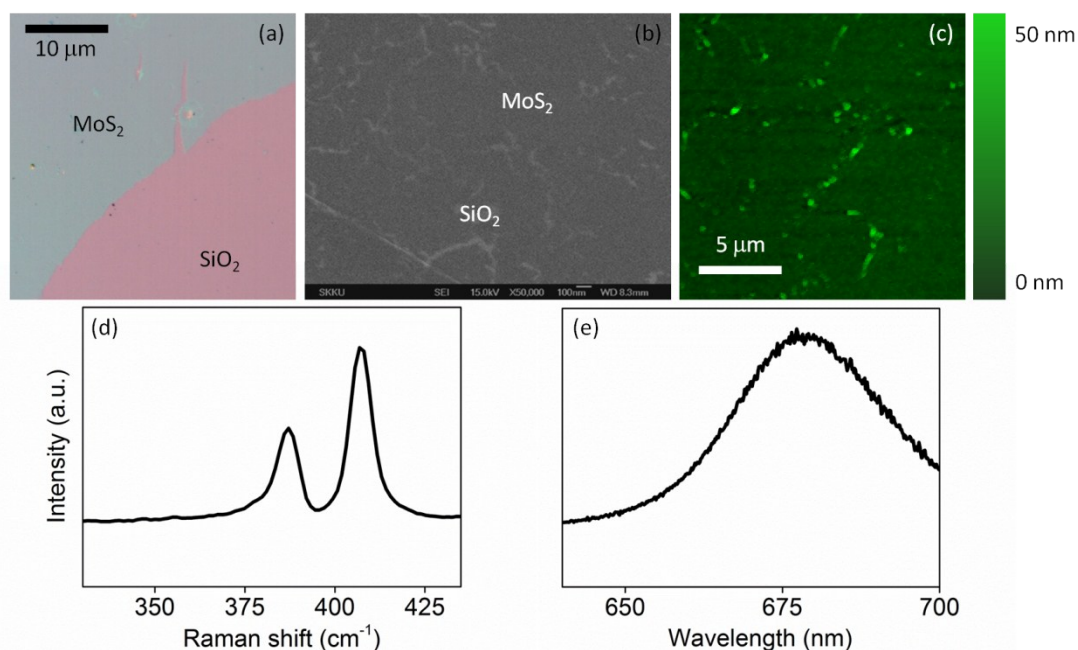


Fig. S2. OM image (a), SEM image (b), AFM image (c), Raman spectrum (d) and PL spectrum (e) of MoS₂ on SiO₂ transferred with common solution etching method.

The transfer process of common solution etching method was shown in Fig. S1. After transfer, PMMA polymer residue was observed in Fig. S2a and S2c as polymer carrier film cannot be completely removed. In Fig. S2b, wrinkles and microcosmic cracks were observed in SEM images, which is due to the locally generated strain. PMMA cannot afford robust mechanical support for MoS₂, thus it is inevitable to introduce strain into MoS₂ layer during this PMMA-mediated transfer process.¹ Raman peak positions in Fig. S2d were down-shifted about 1 cm⁻¹ compared with samples in Fig. 3 in manuscript, due to local strain and/or doping effect from PMMA residues. PL peak in Fig. S2e was also up-shifted about 10 nm.

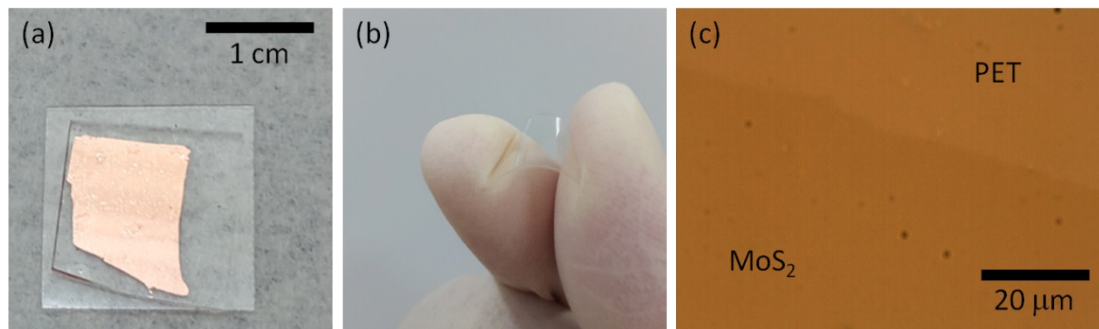


Fig. S3. Optical images of PDMS/PMMA/Cu/MoS₂/PET sample (a), MoS₂ on PET (b) and OM image of transferred MoS₂ film on PET substrate (c).

We transferred MoS₂ to PET substrate, which is widely used as flexible substrate for various applications, by simply replacing SiO₂ target substrate with PET following the same process in Fig. 1. Fig. S3a and S3b clearly show the successful transfer of large-area MoS₂ film onto the PET substrate. Fig. S3c shows the perfect uniformity and cleanness of the transferred MoS₂ film.

References

1. D. L. Ma, J. P. Shi, Q. Q. Ji, K. Chen, J. B. Yin, Y. W. Lin, Y. Zhang, M. X. Liu, Q. L. Feng, X. J. Song, X. F. Guo, J. Zhang, Y. F. Zhang and Z. F. Liu, *Nano Res*, 2015, **8**, 3662-3672.
2. Z. Y. Lin, Y. D. Zhao, C. J. Zhou, R. Zhong, X. S. Wang, Y. H. Tsang and Y. Chai, *Sci Rep-*

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